A new hybrid LDA and Generalized Tight-Binding method for the electronic structure calculations of strongly correlated electron systems

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A novelhybrid scheme is proposed. The ab initio LDA calculation is used to construct the W annier functions and obtain single electron and C oulomb parameters of the multiband H ubbard-typem odel. In strong correlation regime the electronic structure within multiband H ubbard model is calculated by the Generalized T ight-B inding (GTB) method, that combines the exact diagonalization of the model H amiltonian for a small cluster (unit cell) with perturbation treatment of the intercluster hopping and interactions. For undoped La_2CuO_4 and Nd_2CuO_4 this scheme results in charge transfer insulators with correct values of gaps and dispersions of bands in agreement to the ARPES data.

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I. IN TRODUCTION

A conventional band theory is based on the density functional theory (DFT) and on the Local Density Approximation (LDA)2 within DFT. In spite of great success of the LDA for conventionalm etallic systems it appears to be inadequate for strongly correlated electron systems (SCES). For instance, LDA predicts La2CuO4 to be a metal whereas, in reality, it is an insulator. Several approaches to include strong correlations in the LDA m ethod are known, for example LDA+ U^3 and LDA-SIC 4. Both m ethods result in the correct antiferrom agnetic insulator ground state for La2CuO4 contrary to LDA, but the origin of the insulating gap is not correct. It is formed by the local single-electron states splitted by spin or orbital polarization. In these approaches the param agnetic phase of the undoped La₂CuO₄ (above the Neeltem perature $T_{\rm N}$) will be metallic in spite of strong correlation regime U W , where U is the Hubbard Coulom b param eter⁵ and W is a free electron bandwidth. The spectral weight redistribution between Hubbard subbands is very important e ect in SCES that is related to the form ation of the Mott-Hubbard gap in the param agnetic phase. This e ect is incorporated in the hybrid LDA+dynamicalmean eldtheory (DMFT) (for review see Ref. 6,7,8) and LDA++ approaches. 9 The electron selfenergy in LDA+DMFT approach is calculated by the DMFT theory in the \lim it of in nite \dim ension 10,11 and (E). That is why the is k-independent, k (E)! correct band dispersion and the ARPES data for High- T_c compounds cannot be obtained within LDA+DMFT theory. Recent development of the LDA+clusterDMFT m ethod^{14,15} and spectral density functional theory¹⁶ gives som e hopes that non-local corrections m ay be included in this scheme.

A generalized tight-binding (GTB) 17 m ethod has been proposed to study the electronic structure of SCES as a generalization of Hubbard ideas for the realistic multi-

band Hubbard-like models. The GTB method combines the exact diagonalization of the intracell part of the Ham iltonian, construction of the Hubbard operators on the basis of the exact intracell multielectron eigenstates, and the perturbation treatment of the intercell hoppings and interactions. A similar approach to the 3-band p model of cuprates 18,19 is known as the cell perturbation m ethod. 20,21,22 The practical realization of the GTB m ethod for cuprates required an explicit construction of the W annier functions to overcome the nonorthogonality of the oxygen molecular orbitals at the neighboring CuO 6 cells. The GTB calculations for undoped and underdoped cuprates are in good agreement with ARPES data both in the dispersion of the valence band and in the spectral intensity. 23,24 A strong redistribution of spectral weight with hole doping and the form ation of the in-gap states have been obtained in these calculations. Sim ilar G T B calculations for the manganites has been done recently.25

As any model Ham iltonian approach the GTB method is not ab initio, there are many Ham iltonian parameters like intraatom is energy levels of pand delectrons, various per dand per phopping parameters, Coulomb and exchange interaction parameters. These parameters have been obtained by thing the set of optical, magnetic and ARPES 23 data. Generally the question arises how unique the set of parameters is. To overcome this restriction we have proposed in this paper a novel LDA+GTB scheme that allows to calculate the GTB parameters by the ab initio LDA approach.

The paper is organized as follows: In Section II the construction of W annier functions from self-consistent LDA eigenfunctions as well as ab initio parameters of the multiband p d model for LaCuO $_4$ and Nd2CuO $_4$ are given. A brief description of the GTB method is done in Section III. Section IV contains the LDA+GTB band structure calculations for La2CuO $_4$ and Nd2CuO $_4$. The e ective low-energy t $_{\rm S}$ model with ab initio pa-

ram eters is presented in Section V . Section V I is the conclusion .

II. CALCULATION OF AB INITIO PARAMETERS FROM LDA

To obtain hopping integrals for dierent sets of bands included in consideration we apply projection procedure using W annier functions (W Fs) formalism. 31 W Fs were rst introduced in 1937 by W annier 27 as Fourier transformation of B loch states j $_{ik}$ i

$$\mathcal{N}_{i}^{T}i = \frac{1}{P N}^{X} e^{ikT} j_{ik}i; \qquad (1)$$

where T is lattice translation vector, N is the number of discrete k points in the st Brillouin zone and i is band index. One major reason why the WFs have seen little practical use in solid-state applications is their nonuniqueness since for a certain set of bands any orthogonal linear combination of Bloch functions j ik i can be used in (1). Therefore to de ne them one needs an additional constraint. Among others Marzari and Vanderbilt²⁸ proposed the condition of maximum localization for WFs, resulting in a variational procedure. To get a good initial guess authors of Ref.28 proposed to choose a set of localized trial functions j n i and project them onto the Bloch states j ik i. It was found that this starting guess is usually quite good. This fact later led to the simpli ed calculating schem e^{29} where the variational procedure was abandoned as in present work and the result of the aforem entioned projection was considered as the nalstep.

A. W annier function form alism

To construct the W Fs one should to de neaset of trial orbitals j $_n$ i and choose the B loch functions of interest by band indexes (N_1, \ldots, N_2) or by energy interval $(E_1; E_2)$. Non-orthogonalized W Fs in reciprocal f_{nk} i space are then the projection of the set of site-centered atom iclike trial orbitals j $_n$ i on the B loch functions j $_{ik}$ i of the chosen bands:

where $_{i}$ (k) is the band dispersion of i-th band obtained from self-consistent ab initio LDA calculation. In present work we use LMT-orbitals 30 as trial functions. The B loch functions in LMTO basis are denied as

$$j_{ik}i = X c^{k}_{i}j^{k}i;$$
 (3)

where is the combined index representing qlm (q is the atom ic number in the unit cell, l and m are orbital and

m agnetic quantum numbers), k (r) are the B loch sums of the basis orbitals (r T)

k
 (r) = $\frac{1}{P} \frac{X}{N}$ e^{ikT} (r T); (4)

and the coe cients are

$$c^{k}_{i} = h \quad j_{ik} i:$$
 (5)

Since in present work $j_n i$ is an orthogonal LM TO basis set orbital (in other words n in $j_n i$ corresponds to the particular qlm combination), then $h_{ik} j_n i = c_{ni}^k$. Hence

$$\iint_{n_k} i = \iint_{i=N_1}^{x} j_{ik} i c_{n_i}^k = \iint_{i=N_1}^{x^2} X c_{n_i}^k c_{n_i}^k j^k i; \quad (6)$$

In order to orthonormalize the WFs (6) one needs to calculate the overlap matrix $O_{nn^0}(k)$

$$O_{nn^{\circ}}(\mathbf{k}) \qquad \mathbf{M}_{nk} \mathbf{M}_{n^{\circ}k} \mathbf{i} = \sum_{i=N_{1}}^{\mathbf{X}^{i}} c_{ni}^{k} c_{n^{\circ}i}^{k}; \qquad (7)$$

then its inverse square root $S_{nn^0}(k)$ is de ned as

$$S_{nn^0}(k) \qquad O_{nn^0}^{1=2}(k)$$
: (8)

In the derivation of (7) the orthogonality of B loch states h $_{nk}$ j $_{n^0k}$ i = $_{nn^0}$ was used.

From (6) and (8), the orthonorm alized W Fs in k-space y_{nk} i can be obtained as

$$j_{N_{nk}} i = X S_{nn^{\circ}}(k) j_{N_{n^{\circ}k}} i = X^{2} j_{ik} i c_{ni}^{k} ;$$

$$c_{ni}^{\circ} S_{nn^{\circ}}(k) j_{N_{n^{\circ}k}} i = X^{i=N_{1}} S_{nn^{\circ}}(k) c_{n^{\circ}i}^{k} ;$$

Then the matrix element of the Hamiltonian $P^{W\ F}$ in reciprocal space is

Ham iltonian matrix element in real space is

$$H_{nn^0}^{WF}(T) = hW_n^0 \dot{H} \dot{W}_{n^0}^{T} \dot{i} = \frac{1}{N} \times \overset{\dot{X}}{X}^2 + \xi_{n^0 \dot{i} \dot{i}}(k) e^{-ikT};$$

here atom $\,n^0$ is shifted from its position in the primary unit cell by a translation vector T . For more detailed description of this procedure see. 31

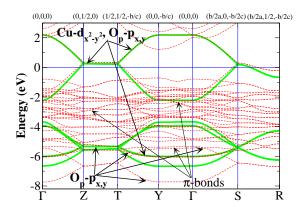


FIG. 1: (Color online) Comparison of the band structure of La_2CuO_4 from LDA calculation (dotted lines) and from projection on the $\text{Cu-d}_{x^2-y^2}$ and $\text{O}_p\text{-p}_x$, $\text{O}_p\text{-p}_y$ set of orbitals (bold solid lines). Ferm i level coresponds to zero energy.

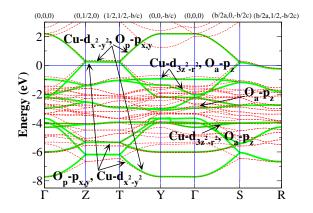
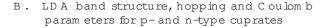


FIG.2: (Coloronline) The same as in Fig.1 but projection is done on the Cu-d_{x² y²}, Cu-d_{3z² r²} and O_p-p_x, O_p-p_y, O_a-p_z set of orbitals.



B asically all cuprates have one or m ore CuO $_2$ planes in their structure, which are separated by layers of other elements (Ba, Nd, La, ...). They provide the carriers in CuO $_2$ plane and according to the type of carriers all cuprates can be divided into two classes: p-type and n-type. In present paper we deal with the simplest representatives of this two classes: La $_2$ $_x$ Sr $_x$ CuO $_4$ (LSCO) and Nd $_2$ $_x$ Ce $_x$ CuO $_4$ (NCCO) correspondingly.

LDA band calculation for La $_2$ CuO $_4$ and Nd $_2$ CuO $_4$ was done within LMTO method 30 using atom ic sphere approximation in tight-binding approach 32 (TB-LMTO-ASA). In the case of Nd $_2$ CuO $_4$ Nd-4f states were treated as pseudocore states.

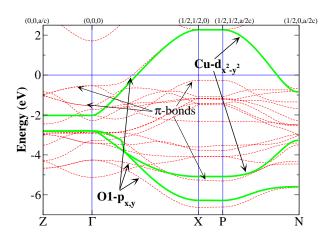


FIG. 3: (Color online) Comparison of the band structure of N d_2 CuO $_4$ from LDA calculation (dotted lines) and from projection on the Cu- $d_x{}^2$ $_y{}^2$, O 1- p_x and O 1- $p_y{}$ set of orbitals (bold solid lines). Ferm i level corresponds to zero energy.

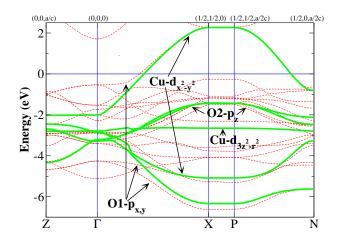


FIG. 4: (Color on line) The same as in Fig. 3 but projection is done on the Cu-d $_{x^2-y^2}$, Cu-d $_{3z^2-r^2}$ and O1-p $_x$, O1-p $_y$, O2-p $_z$ set of orbitals.

La $_2$ CuO $_4$ at the low tem perature and zero doping has the orthorhom bic structure (LTO) with the space group B m ab. 33 The lattice parameters and atom ic coordinates at 10 K were taken from Ref.33 to be a= 5.3346, b= 5.4148 and c= 13.1172 A, La (0, -0.0083, 0.3616), Cu (0, 0, 0), O $_p$ (0.25, 0.25, -0.0084), O $_a$ (0, 0.0404, 0.1837). Here and below O $_p$ denotes in-plane oxygen ions and O $_a$ -apical oxygen ions. In comparison with high temerature teragonal structure (HTT) orthorhom bic La $_2$ CuO $_4$ have two formula units per unit cell and the CuO $_6$ octahedra are rotated cooperatively about the [110] axis. As a result O $_p$ ions are slightly moved of the Cu plane and four in { plane La-O $_a$ bond lengths are unequal.

N d $_2$ C uO $_4$ at the room temperature and zero doping has the tetragonal structure with the space group I4=m m m 34 also called T $^\prime$ -structure. The lattice param e-

ters are a= b= 3.94362, c= 12.1584 A $.^{34}$ Cu ions at the 2a site (0,0,0) are surrounded by four oxygen ions 0 1 which occupy 4c position (0,1/2,0). The Nd at the 4e site (0,0,0.35112) have eight nearest oxygen ions neighbors 0 2 at 4d position (0,1/2,1/4) $.^{34}$ One can imagine bodycentered T'-structure as the HTT structure of La₂CuO₄ but with two oxygen atom smoved from apices of each octahedron to the face of the cell at the midpoints between two oxygen atoms on the neighbouring CuO₂ planes. In other words Nd₂CuO₄ in T'-structure has no apical oxygens around Cu ion.

The LDA band structure of both compounds along the high-symmetry lines in the Brillouin zone is shown in Figs. 1-4 by dotted lines. The coordinates of high-symmetry points in BZ are given on top of each picture. The complex of bands in the energy range (-8, 2.5) eV consists primarily of Cu-3d and O-2p states. The total bandwidths amount 10 eV for La-cuprate and 7 eV for Nd-cuprate. Contribution of Cu-3d and O-2p orbitals to the dierent bands is displayed by arrows.

O ne can see that the band crossing E_F have character of $Cu\text{-}d_{x^2-y^2}$ and $O_p\text{-}p_{x,y}$ for La_2CuO_4 and $Cu\text{-}d_{x^2-y^2}$, $O1\text{-}p_{x,y}$ in the case of Nd_2CuO_4 . It corresponds to antibonding pd orbital. So for hoppings calculation the projection on $Cu\text{-}d_{x^2-y^2}$, $O_p\text{-}p_x$, $O_p\text{-}p_y$ orbitals for Lacuprate and $Cu\text{-}d_{x^2-y^2}$, $O1\text{-}p_x$, $O1\text{-}p_y$ orbitals for Nd-cuprate was done. Such set of orbitals corresponds to the 3-band p - d m odel. The bands obtained by the described in Sec. IIA projection procedure are shown by solid lines in Figs. 1 and 3. It is clearly seen that in case of La_2CuO_4 3-band m odel did not reproduce the band crossing E_F properly (Fig. 1, SR direction).

d m odel didn't provide proper de-Since 3-band p scription of the LDA bands around Ferm i level the projection on more complex set of trail orbitals for both com pounds was done. The resulting bands are plotted by solid lines in Figs. 2 and 4. Corresponding multiband p - d m odel contains Cu-d_{x^2-y^2}, Cu-d_{3z^2-r^2}, O_p p_x , O_p - p_y , O_a - p_z states for La_2CuO_4 and Cu- d_{x^2} v^2 , Cu $d_{3z^2-r^2}$, 01- p_x , 01- p_y , 02- p_z states for N d_2 CuO₄. The energy range for projection was (-8.4, 2.5) eV and (-8, 2)eV for the case of La-cuprate and Nd-cuprate correspondingly. The main e ect of taking into account $Cu-d_{z^2}$ r^2 and O a -pz states for La2CuO 4 is the proper description of the band structure (in comparison with LDA calculation) at the energies up to 2 eV below Ferm i level. From Fig. 3 and 4 one can see that in case of N d₂C uO₄ both sets of trial orbitals properly describe the LDA band crossing the Ferm i level which has $Cu-d_{x^2-v^2}$ sym m etry. At the sam e tim e its bonding part does not agree well with the LDA bands since projection did not include all Cu-d and 0 -p orbitals.

The resulting hopping parameters and energy of particular orbitals for two sets of trial orbitals are presented in Tables I and II. The second column contains the connecting vector T between two sites. It is clearly seen that hoppings decay quite rapidly with distance between ions.

For the multiband p d model the values of

TABLE I:H opping param eters and single electron energies for orthorhom bic La₂CuO₄ obtained in W F projection procedure for di erent sets of trial orbitals (all values in eV). Here x^2 , z^2 , p_x , p_y , p_z denote Cu-d_{x²} $_y$ ², Cu-d_{3z²} $_r$ ², O_p-p_x, O_p-p_y, O_a-p_z orbitals correspondingly. The 3-d and 4-th columns correspond to bases of the 3-band and the multiband p d m odels respectively.

H opping	C onnecting	Cu-x ²	Cu-x ² , z ²	
-11 5	vector	0 p _x , p _y	0 -p _x , p _y , p _z	
		$E_{x^2} = -1.849$	E _{x2} = -1.849	
		$E_{p_x} = -2.767$	$E_{z^2} = -2.074$	
		$E_{p_y} = -2.767$	$E_{p_x} = -2.806$	
		_	$E_{p_y} = -2.806$	
			$E_{p_z} = -1.676$	
$t(x^2,x^2)$	(-0.493 , -0.5)	-0.188	-0.188	
$t^{0}(x^{2},x^{2})$	(-0.985, 0.0)	0.001	0.002	
$t(z^2,z^2)$	(-0.493 , -0.5)		0.054	
$t^{0}(z^{2},z^{2})$	(-0.985, 0.0)		-0.001	
$t(x^2,p_x)$	(0.246,0.25,-0.02)	1.357	1.355	
$t^{0}(x^{2},p_{x})$	(-0.739,0.25,-0.02)	-0.022	-0.020	
$t(z^2,p_x)$	(0.246,0.25,-0.02)		-0.556	
$t^{0}(z^{2},p_{x})$	(-0.739 , 0.25 , -0.02)		-0.028	
$t(z^2,p_z)$	(0,0.04,0.445)		0.773	
$t^0(z^2,p_z)$	(-0.493,-0.46,-0.445)		-0.011	
$t(p_x,p_y)$	(0.493, 0.0)	-0.841	-0.858	
$t^0 (p_x, p_y)$	(0,0.5,0.041)	0.775	0.793	
t ⁰⁰ (p _x ,p _y)	(0.985,0.5,0.041)	-0.001	-0.001	
$t(p_x,p_z)$	(-0.246,-0.21,0.465)		-0.391	
$t^0 (p_x p_z)$	(0.246,0.29,-0.425)		-0.377	
t ⁰⁰ (p _x ,p _z)	(0.246,-0.21,-0.746)		0.018	

Coulomb parameters are also required. For Cu in $\rm La_2CuO_4$ they were obtained in constrained LDA supercell calculations 5 to be U = 10 eV and J = 1 eV . 6 For the N d₂CuO₄ we will use the same values of these parameters.

III. GTB M ETHOD OVERVIEW

As the starting model that rejects chemical structure of the cuprates it is convenient to use the 3-band pull model 18,19 or the multiband pull model of model while the rst one is simplier it lacks for some signicant features, namely importance of $d_{\rm z^2}$ orbitals on copper and portability or bitals on apical oxygen. Non-zero occupancy of $d_{\rm z^2}$ orbitals pointed out in XAS and EELS experiments which shows 2-10% occupancy of $d_{\rm z^2}$ orbitals 38,39 and 15% doping dependent occupancy of $d_{\rm z^2}$ orbitals 40 in allhole doped High-Tc compounds). Henceforth the multiband pull model will be used.

Let us consider the Hamiltonian with the following general structure:

TABLE II: Hopping param eters and single electron energies for N $d_2C\,uO_4$ obtained in W F projection procedure for di erent sets of trial orbitals (all values in eV). Here x^2 , z^2 , p_x , p_y , p_z denote $C\,u^2d_{x^2-y^2}$, $C\,u^2d_{3z^2-r^2}$, $0\,1^2p_x$, $0\,1^2p_y$, $0\,2^2p_z$ orbitals correspondingly. The 3-d and 4-th columns correspond to bases of the 3-band and the multiband p-d m odels respectively.

TT '	G	G 2	2 2
H opping	C onnecting	Cu-x ² ,	$Cu-x^2, z^2$
-	vector	0 p _x , p _y	$0 - p_x, p_y, p_z$
		$E_{x^2} = -1.989$	$E_{x^2} = -1.991$
		$E_{p_x} = -3.409$	$E_{z^2} = -2.778$
		$E_{p_y} = -3.409$	$E_{p_x} = -3.368$
			$E_{p_z} = -2.30$
$t(x^2,x^2)$	(1,0)	0.01	0.01
$t^{0}(x^{2},x^{2})$	(1, 1)	-0.00	-0.00
$t(z^2, z^2)$	(1,0)		0.01
$t^{0}(z^{2},z^{2})$	(1, 1)		0.00
$t(x^2,p_x)$	(0,5,0)	1.18	1.18
$t^{0}(x^{2},p_{x})$	(0.5,1)	-0.06	-0.06
$t^{0}(x^{2},p_{x})$	(1.5,0)	0.04	0.04
$t^{000} (x^2, p_x)$	(1.5,1)	0.00	0.00
$t(z^2,p_x)$	(0,5,0)		-0.29
$t^{0}(z^{2},p_{x})$	(0.5, 1)		0.01
$t(z^2,p_z)$	(0, 0.5, 0.771)		0.10
$t^{0}(z^{2},p_{z})$	(1, 0.5, 0.771)		0.02
t(p _x ,p _y)	(0.5,0.5)	0.69	0.67
$t^0(p_x,p_y)$	(1.5,0.5)	0.00	0.00
t(p _x ,p _z)	(0.5, 0.5, 0.771)		0.02
$t^0(p_x,p_z)$	(0.5,-0.5, 0.771)		0.02

where c_f is the annihilation operator in W annier representation of the hole at site f at orbital $\,$ w ith spin $\,$, n_f $\,$ = c_f^{y} $\,$ c_f $\,$.

In particular case of cuprates and corresponding multiband p dm odel, f runs through copper and oxygen sites, run through d_{x^2} y^2 d_{x^2} and d_{3z^2} r^2 orbitals on copper, p_x and p_y atom ic orbitals on the 0 $_p$ oxygen sites and $p_{\rm z}$ orbital on the apical O $_{\rm a}$ -oxygen; -single-electron energy of the atomic orbital . $T_{\rm fg}$ includes matrix elements of hoppings between copper and oxygen (t_{pd} for hopping d_{x^2} \$ p_x ; p_y ; $t_{pd} = \overline{3}$ for d_{z^2} \$ p_x ; p_y ; t_{pd}^0 for d_{z^2} \$ p_z) and between oxygen and oxygen (t_{pp} for hopping p_x \$ p_y ; t_{pp}^0 for hopping $p_x; p_y \$ p_z). The Coulomb matrix elements V_{fa} includes intraatom ic Hubbard repulsions of two holes with opposite spins on one copper and oxygen orbital (Ud, Up), between di erent orbitals of copper and oxygen (Vd, Vp), Hund exchange on copper and oxygen (J_d, J_p) and the nearest-neighbor copper-oxygen C oulom b repulsion Vpd.

GTB m ethod 17,23,24 consist of exact diagonalization of intracell part of the multiband Hamiltonian (10) and perturbative account of the intercell part. For La $_2$ $_x$ Sr $_x$ CuO $_4$ and Nd $_2$ $_x$ Ce $_x$ CuO $_4$ the unit cells are CuO $_6$ and CuO $_4$ clusters, respectively, and a problem of nonorthogonality of the molecular orbitals of adjacent cells is solved by an explicit fashion using the diagonalization in k-space 41 . In a new symmetric basis the intracell

part of the total H am iltonian is diagonalized, allowing to classify all possible elective quasiparticle excitations in CuO2-plane according to a symmetry. To describe this process the H ubbard X-operators 42 X $_{\rm f}^{\rm m}$ 5 X $_{\rm f}^{\rm p/q}$ pilogare introduced. Index m $_{\rm f}$ (p;q) enumerates quasiparticle with energy $!_{\rm m}$ = " $_{\rm p}$ (N + 1) = " $_{\rm q}$ (N), where " $_{\rm p}$ is the p-th energy level of the N-electron system. There is a correspondence between H ubbard operators and single-electron creation and annihilation operators:

$$c_{f} = \begin{pmatrix} X \\ m \end{pmatrix} X_{f}^{m}; \qquad (11)$$

where (m) determ ines the partial weight of a quasiparticle m with spin and orbital index . Using this correspondence we rewrite the H am iltonian (10)

This Ham iltonian, actually, have the form of the multiband Hubbard model.

D iagonalization of the H am iltonian (10) m entioned above gives energies " $_{\rm p}$ and the basis of H ubbard operators X $_{\rm f}^{\rm m}$. Values of the hoppings,

$$t_{fg}^{m m 0} = X T_{fg}^{0} \quad (m) \quad (m^{0});$$
 (13)

are calculated straightforwardly using the exact diagonalization of the intracell part of the H am iltonian (10).

A gain, in particular case of multiband p d model, the essential for cuprates multielectron con gurations are $d^{10}p^6$ (vacuum state $\mbox{\tt Di}$ in a hole representation), single-hole con gurations d^8p^6 , d^9p^5 , $d^{10}p^4$, $d^{10}p^5p^5$. In the single-hole sector of the H ilbert space the b_{1g} molecular orbital, that we will denote later as j i = f j'i; j'ig, has the minimal energy. In the two-hole sector the lowest energy states are singlet state ji with $^1A_{1g}$ symmetry, that includes Zhang-R ice singlet among other local singlets, and triplet states ji = ji M i M = +1;0; 1) with $^3B_{1g}$ symmetry. 23,24,41 A ll these states form the basis of the H am iltonian (12), and they are shown together with quasiparticle excitations between them in the Fig. 5.

In this basis relations (11) between annihilation—creation operators c_f and Hubbard X-operators X $_f^{\,m}$

$$\begin{split} &c_{\text{fd}_{x^2}} &= uX_{\text{f}}^{0;} + 2_{x}X_{\text{f}}^{iS};\\ &c_{\text{fp}_{\text{b}}} &= vX_{\text{f}}^{0;} + 2_{\text{b}}X_{\text{f}}^{iS};\\ &c_{\text{fp}_{\text{a}}} &= a(\frac{p_{x_{\text{f}}}^{2}}{2X_{\text{f}}^{iT0}} X_{\text{f}}^{iT2});\\ &c_{\text{fd}_{z^2}} &= z(\frac{2X_{\text{f}}^{iT0}}{2X_{\text{f}}^{iT0}} X_{\text{f}}^{iT2});\\ &c_{\text{fp}_{\text{z}}} &= p(\frac{p_{x_{\text{f}}}^{2}}{2X_{\text{f}}^{iT0}} X_{\text{f}}^{iT2});\\ \end{split}$$

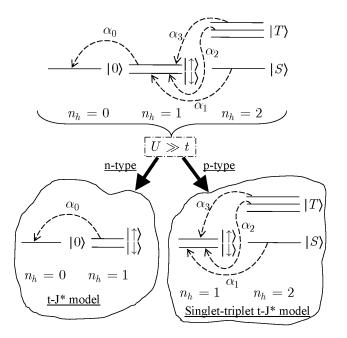


FIG. 5: Schematic picture of states and quasiparticle excitations between them in Hubbard-type m odel (12). Here $n_{\rm h}$ stands for number of holes, i numerates Fermitype quasiparticles, states Di, j i, Bi, T i represents basis of the H am iltonian (12). A lso, bases of e ective models are shown.

and the explicit form of the Hamiltonian (12) is given by

$$H_{pd} = \begin{bmatrix} X & h & X \\ & & &$$

. The relation between e ective hoppings (13) in this Ham iltonian and microscopic parameters of the multiband p d m odel is as follow $\3,44 :

$$\begin{array}{llll} t_{fg}^{00} & = & 2t_{pd} \ _{fg} 2uv & 2t_{pp} \ _{fg} v^{2}; \\ t_{fg}^{SS} & = & 2t_{pd} \ _{fg} 2 \ _{x} \ _{b} & 2t_{pp} \ _{fg} \ _{b}^{2}; \\ t_{fg}^{DS} & = & 2t_{pd} \ _{fg} (v \ _{x} + u \ _{b}) & 2t_{pp} \ _{fg} v \ _{b}; \\ t_{fg}^{TT} & = & \frac{2t_{pd}}{3} \ _{fg} 2 \ _{a} \ _{z} + 2t_{pp} \ _{fg} \ _{a} & 2t_{pp} \ _{fg} 2 \ _{p} \ _{a}; \\ t_{fg}^{ST} & = & \frac{2t_{pd}}{3} \ _{fg} z + 2t_{pp} \ _{fg} \ _{a} & 2t_{pp} \ _{fg} p \ _{fg}; \end{array}$$

The factors , , , are the coe cients of W annier transformation made in the GTB method and u, v, $_{x}$, $_{b}$, $_{a}$, $_{p}$, $_{z}$ are the matrix elements

TABLE III: Hopping parameters and single-electron energies of holes obtained by tting GTB band structure to experim ental data and in the ab initio calculations for p- and n-type cuprates (all values in eV).

	1	p-type	n-type		
	tted	ab initio	tted	ab initio	
d _{x 2}	0	0	0	0	
"px	1.5	0.91	1.4	1.38	
$^{"}d_{z^2}$	0.2	0.14	0.5	0.79	
" pz	0.45	-0.26	0.45	0.31	
t _{pd}	1	1	1	1	
t _{pp}	0.46	0.63	0.56	0.57	
t_{pd}^0	0.58	0.57	0	80.0	
tpp tpo tpp	0.42	0.29	0.1	0.02	

of annihilation-creation operators in the Hubbard Xoperators representation²³.

Calculations^{23,24} of the quasiparticle dispersion and spectral intensities in the fram ework of the multiband d model by the GTB method are in very good agreem ent to the ARPES data on insulating compound Sr₂CuO₂Cl₂. 45,46 Other signicant results of this method are^{47,48}:

i) pinning of Ferm i level in LSCO at low concentrations was obtained in agreement with experiments. 49,50 This pinning appears due to the in-gap state, spectral weight of this state is proportional to doping concentration x and when Ferm i level com es to this in-gap band then Ferm i level \pins" there. The localized in-gap state exist in NCCO also for the same reason as in LSCO, but its energy is determined by the extremum of the band at (=2; =2) point and it appears to be above the bottom of the conductivity band. Thus, the rst doped electron goes into the band state at the (;0) and the chemical potential for the very small concentration merges into $_{
m O}$ the band. At higher x it m eets the in-gap state with a pinning at 0.08 < x < 0.18 and then again moves into the band. The dependence (x) for NCCO is quite asymmetrical to the LSCO and also agrees with experimental $x_{\rm f}^{\rm TT}$ ($x_{\rm f}^{\rm TT}$); $x_{\rm f}^{\rm TT}$); $x_{\rm g}^{\rm TT}$); $x_{\rm g}^{\rm TT}$); (14) metrical to the LSCO and also agrees with experimental the band. The dependence (x) for NCCO is quite asymdata;50

> ii) experim entally observed⁵¹ evolution of Ferm i surface with doping from hole-type (centered at (;)) in the underdoped region to electron-type (centered at (0;0)) in the overdoped region is qualitatively reproduced:

> iii) pseudogap feature for LSCO is obtained as a low ering of density of states between the in-gap state and the states at the top of the valence band.

> In all these calculations the set of the microscopic model parameters, obtained by tting to experimental ARPES data, 45,52 was used. Hoppings and singleelectron energies are listed in Table III, values of Coulom b param eters are as follows:

$$U_d = V_d = 9; U_p = V_p = 4;$$

 $J_d = 1; J_p = 0; V_{pd} = 1:5:$ (16)

All results above were obtained treating the intercell hopping in the Hubbard-I approximation. But the GTB method is not restricted to such a crude approxim ation. The Fourier transform of the two-time retarded Green function in energy representation can be rewritten in terms of matrix G reen function D_k^{mn} (E) =

$$X_k^m$$
 X_k^n Y :
$$DD \qquad EE \qquad X$$

$$C_k \qquad C_k^y \qquad = \qquad (m) \qquad (m^0) D_k^{mm^0} (E):$$

The diagram technique for Hubbard X-operators is $\mbox{developed}^{53,54}$ and the generalized Dyson equation 55

$$\hat{D_k} \quad (\!E\!) = \quad \hat{G_k}^{(0)} \quad (\!E\!) \quad + \hat{f_k} \quad (\!E\!) \quad \hat{P_k} \quad (\!E\!) : (17)$$

Here, \hat{k} (E) and $\hat{P_k}$ (E) are the self-energy and the strength operators, respectively. The presence of the strength operator is due to the redistribution of the spectral weight, that is an intrinsic feature of SCES. First time it was introduced in the spin diagram technique and called \a strength operator"56 because the value of $\hat{P_k}$ (E) determines an oscillator strength of excitations. It is also should be stressed, that \hat{k} (E) in Eq. (17) is the self-energy in X-operators representation and therefore it is di erent from the self-energy entering Dyson equation for the G reen function $c_k c_k^y$

G reen function $\hat{G}_k^{(0)}$ (E) is de ned by the formula $\hat{G}_k^{(0)}$ (E) $\hat{G}_k^{(0)}$ (E) $\hat{G}_k^{(0)}$ (E) \hat{f}_k (E) \hat{f}_k ;

$$\hat{G}_{k}^{(0)} (E)^{1} = \hat{G}_{0}^{1} (E) \quad \hat{P}_{k} (E) \hat{f}_{k};$$
(18)

where \hat{G}_0^{-1} (E) is the free propagator and \hat{f}_k is the interaction m atrix element (for the Hubbard model, $t_k^{m m} =$ (m) (m $^{0})\,t_{k}$, and G $_{0}^{\,m\,m\,^{\,0}}$ (E) = $_{m\,m\,^{\,0}}$ (iE

In the Hubbard-I approximation at U W the selfenergy \hat{k} (E) is equal to zero and the strength operator P_k^{mn} (E) is replaced by P_E^{mn} (E)! $P^{mn} = {}_{mn}F^m$, where $F^{m} = X_{f}^{p,p} + X_{f}^{q,q}$ is the occupation factor. So, in this approximation the following equation is derived from Eq. (17):

$$\hat{D}_{k}^{(0)} = \hat{G}_{0}^{1} \times E \quad \hat{P} \cdot \hat{f}_{k} \quad \hat{P} : \quad (19)$$

U sing diagram technique for the X-operators it is possible to nd solution in the GTB method beyond the Hubbard-I approximation. But such discussion is far from the scope of this paper's goals.

It should be stressed that the GTB bands are not free electron bands of the conventional band structure, these are the quasiparticle bands with the number of states in each particular band depending on the occupation num ber of the initial and nal multielectron con gurations, and thus on the electron occupation. Bands with zero spectral weight or spectral weight proportional to doping value x appear in the GTB approach.

IV. LDA+GTB M ETHOD: RESULTS AND D ISC II SS TO N

In this Section wew ill describe the LDA+GTB method itself and som e results of this approach.

In LDA+GTB schemeallparameters of the multiband model are calculated within the ab initio LDA (by W annier function projection technique, see Sec. IIA) and constrained LDA method.35 Analysis of the LDA band structure gives the minimal model that should be used to describe the physics of system under consideration. Although LDA calculation does not give correct description of the SCES band structure, it gives ab initio param eters and reduced number of essential orbitals or the \m in im al reliable model". Then, the e ects of strong electron correlations in the fram ework of this model with ab initio calculated param eters are explicitly taken into account within the GTB method and the quasiparticle band structure is derived.

In Section II the ab initio calculations for undoped La_2CuO_4 and Nd_2CuO_4 are presented. One can see that in the 3-band model (Figs. 1 and 3) it is possible to describe the top of the valence band but not the lower lying excitations withing 4 eV. The main e ect of taking into account Cu-d_{3z² r²} and O_a-p_z states for La₂CuO₄ system is the proper description of the band structure (in comparison with LDA calculation) at the energies up to 4 eV below Fermilevel (see Fig. 2). Of course, the ab initio LDA band structure is not correct in undoped cuprates, but it gives an indication what orbitals should be included in more appropriate calculations. Therefore if one needs to describe quantitatively the low-energy excitations of La₂ $_x$ Sr_xCuO₄, the Cu-d_{3z² r² and O_a-p_z} orbitals should be taken into account and the reliable m in im alm odel is them ultiband p dm odel. In N d C uO 4 the Cu- $d_{3z^2-r^2}$ and O2- p_z states does not contribute signi cantly to the band structure (com pare Figs. 3 and 4) and the minimal model is the 3-band p d model. Nevertheless to treat p-and n-type cuprates on equal footing laterwewilluse the samemultibandp dmodelforboth LSCO and NCCO with di erent material dependent param eters. Hopping param eters decay rapidly with distance (see Tables I and II) so in GTB calculation we will use only nearest copper-oxygen and oxygen-oxygen hoppings which are listed in Table III.

In Refs. 57,58 ab initio calculations were done for $YBa_2Cu_3O_7$ and La_2CuO_4 , and single-electron energy $\mathbf{v}_{p_x} = 0.9 \text{ eV}$ was obtained. This value is very close to the one presented in Table III. But in Refs. 57,58 the Cus states were taken into account with energy $"_s =$ eV.OurLDA calculations shows that Cu-s bands contributes to the band structure shown in Figs. 2 and 4 at approximately 7 eV below and at 2 eV above Fermi level. Therefore Cu-s states does not contribute significantly to the low-energy physics. But these states can contribute to the e ective intraplane hopping param eters t^0 and t^{00} between the nearest and next-nearest neighboring unit cells. In our LDA+GTB m ethod Cu-s states are

neglected. It could be a reason why for La_2CuO_4 our $t^0\!=\!t=0:\!137$ (see Table IV) is less then $t^0\!=\!t=0:\!17$ obtained in Ref. 58, where in uence of Cu-s orbital on hoppings was taken into account.

There is a claim that pd -bonds⁵⁹ and non-bonding oxygen states⁶⁰ are very im portant in low-energy physics of High-Tc cuprates. To discuss this topic lets start with analysis of ab initio calculations. Present LDA calculations show that anti-bonding bands * of -bonds (Cu-d+0-p, see Figs. 1 and 3) situated slightly below anti-bonding a^* bands of $Cu-d_{3z^2}$ $r^2+O_a-p_z$ origin in La₂CuO₄ and slightly above anti-bonding a* bands of $Cu-d_{3z^2}$ r^2 origin in Nd_2CuO_4 (see Figs. 2 and 4). GTB calculations²³ show that states corresponding to $_{\rm a}$ * band contributes to the $a_{1\rm q}$ m olecular orbital in the single-hole sector of the Hilbert space. This alg molecular orbital situated above b_{1q} state j i = f J i; # ig byan energy about 12 eV. From the relative position of a * and * bands in LDA calculations we conclude that the energy of molecular orbital corresponding to the * band will be situated around energy of a_{1q} state. Therefore, it will be above ji state by about 1:0 1:4 eV. Also, both states corresponding to * and a * are empty in undoped com pound and spectral weight of quasiparticle excitations to or from these states will be zero. Sum marizing, -bonds, as well as a * states, will contribute to the GTB dispersion only upon doping and only in the depth in the valence band below 1 eV from the top. Moreover, since energy di erence between triplet Ti and singlet \$i states is about 0.5 eV, 23 the contribution from the singlet-triplet excitations will be much more important to the low-energy physics. Although, -bonds could be im portant for explanation of som e optical and electronenergy loss spectroscopy experim ents, but in description of low-energy physics of interest they could be neglected. The non-bonding oxygen states contribute to the valence band with energy about 2 3 eV below the top. That is why we will not take -bonds and non-bonding oxygen states in our further consideration.

Now we have an idea whatmodel should be used and ab in itio microscopic parameters of this model. As described in Section III, the GTB method is appropriate method for description of SCES in Mott-Hubbard type insulators and it's results are in good agreement with experimental data. Then it is natural to use this method to work with the ab in itio derived multiband period of model.

The parameters (15) of the Ham iltonian in the GTB method derived from ab initio one are presented in Tables IV and V for p- and n-type cuprates, respectively. Single-electron energies (in eV) and matrix elements of annihilation-creation operators in the X-operators representation were calculated for both LSCO:

$$_{1}$$
 = 1:919; $_{2S}$ = 2:010; $_{2T}$ = 1:300; $_{2T}$ = 0:707; $_{2S}$ = 0:619; (20) $_{2S}$ = 0:987; $_{2S}$ = 0:032; $_{2S}$ = 0:962; $_{2S}$ = 0:237;

TABLE IV: Param eters of the multiband Hubbard model (12) and exchange integral J for LSCO obtained in the framework of the LDA+GTB method (all values in eV). Hoppings giving main contribution to the top of the valence band are shown by bold type.

	t ⁰⁰	t ^{s s}	t ^{os}	t ^{T T}	ť⁵™	J
(0,1)	0.453	0.679	0.560	0.004	-0.086	0.157
(1,1)	-0.030	-0.093	-0.055	-0.001	0	0.001
(0 , 2)	0.068	0.112	0.087	0.002	-0.016	0.004
(2 , 1)	0.003	-0.005	0	0	-0. 002	0

TABLE V: The same as in Table IV, but for NCCO. Hoppings giving main contribution to the bottom of the conductivity band are shown by bold type.

	t ⁰⁰	t ^{s s}	t ^{0s}	t ^{T T}	t ^{s ™}	J
(0,1)	0.410	0.645	-0.523	0	-0.0052	0.137
(1,1)	-0.013	-0.076	0.035	0	0	0.001
(0 , 2)	0.058	0.104	-0.078	0	-0.0002	0.003
(2 , 1)	0.005	-0.002	-0.003	0	-0.0004	0

and NCCO:

$$_{1}$$
 = 1:660; $_{2S}$ = 1:225; $_{2T}$ = 0:264; $_{2S}$ = 0:655; $_{x}$ = 0:626; (21) $_{2S}$ = 0:984; $_{3S}$ = 0:008; $_{2S}$ = 0:997; $_{2S}$ = 0:037:

It is known 61 that sign of the hoppings in the t $\,t^0\,$ J m odel changes during electron-hole transform ation of the operators. Therefore, t $\,$ will have di $\,$ erent signs in p- and n-type cuprates. In present paper we don't do electron-hole transform ation of the operators and both t $\,$ the $\,$ J* and singlet-triplet t $\,$ the $\,$ J* m odels are written using hole operators. Because of that there is no di $\,$ erence in signs of the hoppings t $\,$ for the hole and electron doped systems presented in Tables IV and V .

As the next step we calculate the band structure of the undoped antiferrom agnetic (AFM) insulating cuprate within the GTB method. Results for both GTB method with tting parameters and LDA+GTB method with abinitio parameters (Table III) are presented in the Fig. 6 for La₂CuO₄ and in the Fig. 7 for Nd₂CuO₄.

The GTB band structure obtained for both phenom enological and ab initio sets of param eters is almost identical: the valence band, located below 0 eV in gures, and the conductivity band, located above + 1.5 eV, divided by the insulator gap of the charge transfer origin E $_{\rm ct}$ 2 eV; the undoped LąCuO $_4$ and Nd2CuO $_4$ are insulators in both antiferrom agnetic and param agnetic states. In-gap states at the top of the valence band and about the bottom of the conductivity band are shown by dashed lines. Their spectral weights and dispersions are proportional to doping x and concentration of magnons 62 . Therefore, for undoped compounds, in the Hubbard-I approximation used in GTB method, these states are dispersionless with zero spectral weight.

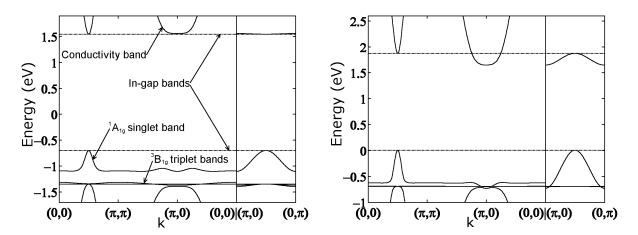


FIG.6: The AFM band structure of La_2CuO_4 obtained in the GTB m ethod with phenomenological set of parameters (left) and in the LDA+GTB m ethod (right). In the left gure bands are labelled; in other GTB band structure gures relative positions of bands are the same.

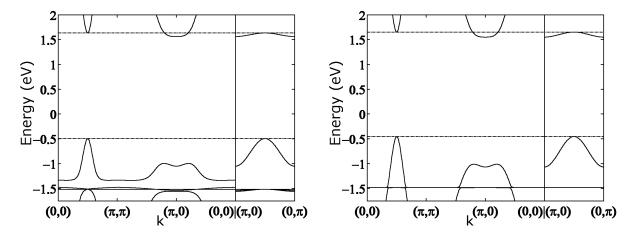


FIG.7: The AFM band structure of N d_2 CuO $_4$ obtained in the GTB m ethod with phenom enological set of param eters (left) and in the LDA+GTB m ethod (right).

The valence band have bandwidth about 6 eV and consists of a set of very narrow subbands with the highest one at the top of the valence band - the so-called \Zhang-Rice singlet" subband. The dominant spectral weight in the singlet band stems from the oxygen p-states, while for the bottom of the empty conductivity band it is from $d_{x^2-y^2}$ -states of copper. Both methods give small, less then 0.5 eV, splitting between the 1A 1g Zhang-Rice-type singlet band and 3 B $_{1g}$ narrow triplet band located below the singlet band (e.g. in the Fig. 7 for Nd_2CuO_4 it is located at $-1.5 \; \text{eV}$). The energy of Cu-d_{3z² r²} orbitalplays the dominant role in this splitting in the GTB method. For La_2CuO $_4$ energy $\textbf{"}_{\text{d}_{,2}}$ is sm aller then for Nd_2CuO $_4$ (see Table III). This results in smaller width of the singlet band for the LSCO compared to the NCCO: about 0.5 eV and 1 eV correspondingly.

However, for La_2CuO_4 m inor discrepancies occurs in the dispersion of the bottom of the conductivity band

near (;0) point obtained by GTB with phenom enological set of parameters and by LDA+GTB. This leads to the di erent character of the optical absorption edge in two presented methods. The absorption edge for the LDA+GTB is formed by the indirect transitions in contrast to the GTB method with phenomenological set of param eters, where the momentum of excited quasiparticle is conserved by optical transition at the absorption edge. For Nd₂CuO₄ both GTB method with tting param eters and LDA+GTB result in the conductivity band minima at the (;0) point (see Fig. 7). Also, in the LDA+GTB method the triplet band dispersion and the singlet-triplet hybridization are much smaller then in the GTB method with thing parameters. This happens mainly due to the smaller values of t_{pp}^0 used in LDA+GTB method, because it is this microscopic param eter that gives main numerical contribution (see Eqs. (15), (20) and (21)) to the t_{fg}^{TT} and t_{fg}^{ST} - hoppings that determ ines the triplet band dispersion and the singlet-triplet hybridization respectively. So, despite som e m inor discrepancies, both G T B m ethod with phenom enological parameters and LD A + G T B m ethod without free parameters gives similar band dispersion.

Next topic that we will discuss in connection to the LDA+GTB method is the value of magnetic moment on copper M $_{\text{C}\,\text{u}}\,\text{.}$ From the neutron di raction studies of $La_2CuO_4^{63}$ and $YBa_2Cu_3O_6^{64}$ it is known that M_{Cu} is equal to 0.5_{B} where $_{B}$ is Bohrm agneton. There are two reasons of why M $_{\text{C}\,\text{u}}$ is dierent from the free atom ic value 1:14 B in S = 1=2 C u^{2+} , namely zero temperature quantum spin uctuations and the covalent e ect. Since each oxygen have two neighboring coppers belonging to di erent magnetic sublattices the total moment on oxygen is equal to zero. But due to p d hybridization the pstates of oxygen are partially led so these orbitals could carry non-zero m agnetic m om ent M $_{\odot}$, while total m om ent on oxygen will be equal to zero. Such space distribution of magnetic moment leads to the dierence between experim entally observed antiferrom agnetic form factor for La2CuO4 and the Heisenberg form -factor of Cu²⁺. In order to take into account covalent e ects and zero quantum uctuations on equal footing we will write down the expression for M $_{Cu}$:

$$M_{Cu} = 2.28_{B} \text{ hs}^{z} \text{iu}^{2};$$
 (22)

where zero quantum spin uctuations are contained in hS z i and covalent e ects are described by the weight uf of the d 9 pf con guration. The last quantity is calculated in the fram ework of the LDA+GTB method and equal to $u^2=0.5$. In paper 66 the value hS z i = 0.3 was obtained self-consistently in the e ective quasi-two-dimensionalH eisenberg antiferrom agnetic model for typical in La₂CuO₄ ratio 10^{-5} of the interplane and intraplane exchange parameters. Close value of hS z i = 0.319 was obtained in Ref. 67 where also the plaquette ringexchange was considered in Heisenberg Hamiltonian. Using Eq. (22) and above values of u^2 and hS u^2 i we have calculated magnetic moment on copper M u^2 cu = u^2 culated magnetic moment on copper M u^2 cu = u^2 culated magnetic moment on copper M u^2 culated magnetic moment on severed M u^2 cu

Sum m arizing this section, we can conclude that the proposed LDA+GTB scheme works quite well and could be used for quantitative description of the High-T $_{\rm C}$ cuprates. The LDA+GTB scheme also can be used for wide class of SCES – cuprates, m anganites, and other.

V. EFFECTIVE LOW -ENERGY MODEL

When we are interested in the low-energy physics (like e.g. superconductivity) it is useful to reduce the microscopic model to more simpler elective Hamiltonian. For example, for the Hubbard model in the regime of strong correlations the elective model is the to J^* model (to J model plus 3-centers correlated hoppings H_3) obtained by exclusion of the intersubband hoppings perturbatively. 68,69,70 Analysis of the 3-band

m odel results in the e ective Hubbard and the t m odel. 20,22,71,72,73

As the next step we will formulate the e ective model for the multiband p d model. Simplest way to do it is to neglect completely contribution of two-particle triplet state ${}^{3}\mathrm{B}_{1q}$. Then there will be only one low-energy twoparticle state { Zhang-Rice-type singlet ${}^{1}A_{1q}$ { and the e ective model will be the usualt J* model. But in the multiband p d model the di erence T s between energy of two-particle singlet and two-particle triplet depends strongly on various model parameters, particularly on distance of the apical oxygen from the planar oxygen, energy of the apical oxygen, di erence between energy of d_{z^2} -orbitals and d_{x^2} -orbitals. For the realistic values of m odelparam eters T is close to 0.5 eV 24,41 contrary to the 3-band m odelw ith this value being about 2 eV. To take into account triplet states we will derive the e ective Ham iltonian for multiband p d model by exclusion of the intersubband hopping between low (LHB) and upper (UHB) Hubbard subbands. These subbands divided by the energy of charge-transfer gap Ect 2 eV (sim ilar to U in the Hubbard model) and using perturbation theory, sim ilar to Ref. 69, with small parameter W = U we can derive separate e ective models for UHB and LHB. This procedure is schematically shown in Fig. 5. And, as one can see, since the UHB and LHB in initial model (14) are form ed by di erent quasiparticles (nam ely, 0 for LHB and $_1$, $_2$, $_3$ for UHB in Fig. 5), the e ective models will be di erent for upper (valence band, hole doped) and lower (conductivity band, electron doped) subbands.

We write the Ham iltonian in the form $H = H_0 + H_1$, where the excitations via the charge transfer gap E_{ct} are included in H_1 . Then we de ne an operator $H() = H_0 + H_1$ and make the unitary transformation $H() = \exp(i\hat{S})H()\exp(i\hat{S})$. Vanishing linear in component of H() gives the equation for matrix \hat{S} : $H_1 + i H_0; \hat{S} = 0$. The elective Ham iltonian is obtained in second order in and at H() is given by $H() = H_0 + \frac{1}{2}i H_1; \hat{S}$. For the multiband H() denoted the usual of H() in case of electron doping we obtain the usual of H() model describing conductivity band:

$$H_{t J} = \begin{array}{c} X \\ & \text{"}_{1}X_{f}; \\ & \text{f}; \\ & \text{feg;} \end{array} \begin{array}{c} X \\ & \text{then } 100 \\ & \text{feg;} \\ & \text{fegen}; \end{array} \begin{array}{c} X \\ & \text{fegen}; \\ & \text{fegen}; \end{array} \begin{array}{c} X \\ & \text{fegen}; \end{array}$$

$$+ \begin{array}{c} X \\ & \text{J}_{fg} \\ & \text{fegen}; \end{array} \begin{array}{c} X \\ & \text{fegen}; \end{array} \tag{23}$$

here H $_3$ contains three-centers interaction terms given by Eq. (A1), $S_{\rm f}$ are spin operators and $n_{\rm f}$ are number of particles operators. The $J_{\rm fg}=2$ $t_{\rm fg}^{\rm OS}$ =E $_{\rm ct}$ is the exchange parameter.

For p-type systems the e ective H am iltonian has the form of the singlet-triplet t J*m odel describing valence

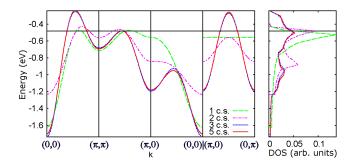


FIG. 8: (Color online) Quasiparticle dispersion and corresponding densities of states (DOS) in the t J^* model calculated for di erent number of taken into account coordination spheres (c.s.). Chem ical potential shown by the straight horizontal line was calculated self-consistently assuming 15% holes doping.

band:

Three-centers interaction terms H_{eff3} are given by Eq.(A2). Expressions for H_0 and H_t are as the follows:

The resulting Ham iltonian (24) is the two-band generalization of the t J^* model. Signi cant feature of effective singlet-triplet model is the asymmetry for n-and p-type systems which is known experimentally. So, we can conclude that for n-type systems the usual t J^* model takes place while for p-type superconductors with complicated structure on the top of the valence band the singlet-triplet transitions are important.

Contrary to the multiband p d model's parameters that fall with distance rapidly, e ective model parameters do not decrease so fast. This happens due to weak distance dependence of W annier functions that determine coe cients fg, fg, fg, fg, fg, fg, fg which, in turn, determine distance dependence of e ective model parameters (15).

To demonstrate the importance of hoppings to far coordination spheres (c.s.) in the Fig. 8 we present the dispersion and DOS in the t J^* model with parameters from Table IV. The electron G reen function (17) has been calculated beyond the Hubbard-I approximation by a decoupling of static correlation functions that

Recent ARPES experim ents 75 show that the Ferm ivelocity $v_{\rm F}=E_{\rm F}=k_{\rm F}$ is nearly constant for wide range of p-type m aterials and doping independent within an experim ental error of 20% . We have calculated this quantity in the to J^* model with parameters from Table IV in the approximation described above. In the doping range from x=0.03 to x=0.15 our calculations give very weak doping dependence of the Fermi velocity. Assuming the lattice constant equal to 4A we have $v_{\rm F}$ varying from 1.6 eVA 1 to 2.0 eVA 1 . Taking into account experimental error of 20% our results is very close to the experimental one.

VI. CONCLUSION

The approach developed here assumes the multiband Ham iltonian for the real crystal structure and its mapping onto low-energy model. Parameters of the elective model (15) are obtained directly from ab initio multiband model parameters. The sets of parameters for the elective models (23) and (24) are presented in Tables IV and V for p- and n-type cuprates, correspondingly.

The e ective low-energy model appears to be the t ℓ ℓ^0 J^* model (23) for N d C uO d and the singlet-triplet t ℓ ℓ^0 J^* model (24) for L d C uO d. There is almost no dierence in the band dispersion with addition of numerically small hoppings to 4-th, 5-th, etc. neighbors.

Sum marizing, we have shown that the hybrid LDA+GTB method incorporate the ab initio calculated parameters of the multiband p $\,$ d model and the adequate treatment of strong electron correlations.

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APPENDIX A: EXPRESSIONS FOR 3-CENTERS
CORRELATED HOPPINGS IN EFFECTIVE
MODELS

In the t J*m odel (23) the 3-centers correlated hoppings are given by:

$$H_{3} = \frac{t_{fm}^{0S} t_{mg}^{0S}}{E_{ct}} X_{f}^{0} X_{m} X_{g}^{0} X_{f}^{0} X_{m} X_{g}^{0} : (A1)$$

The three-centers interaction term sH_{eff3} in the e ective H am iltonian (24) are much more complicated then in the t J*m odeldue to additional triplet and singlet-triplet contributions:

$$H_{eff3} = \frac{t_{fm}^{OS} t_{mg}^{OS}}{E_{ct}} H_{3}^{SS} \qquad v_{E_{ct}}^{OS} t_{3}^{ST} + v^{2} \frac{t_{fm}^{ST} t_{mg}^{ST}}{E_{ct}} H_{3}^{TT};$$
(A 2)

$$H_3^{SS} = X_f^S X_m X_q^S X_f^S X_m X_q^S$$
;

$$H_{3}^{ST} = \frac{1}{2} X_{f}^{T0} X_{m} X_{g}^{S} X_{f}^{T0} X_{m} X_{g}^{S}$$

$$+ 2 X_{f}^{T2} X_{m} X_{g}^{S} + X_{f}^{T2} X_{m} X_{g}^{S}$$

$$+ \frac{1}{2} X_{f}^{S} X_{m} X_{g}^{T0} X_{f}^{S} X_{m} X_{g}^{T0}$$

$$2 X_{f}^{S} X_{m} X_{g}^{T2} X_{f}^{S} X_{m} X_{g}^{T2}$$

$$\begin{array}{lll} \mathbf{H}_{3}^{\,\mathrm{TT}} & = & \frac{1}{2} \, \, \mathbf{X}_{\,\mathrm{f}}^{\,\mathrm{T}\,0} \mathbf{X}_{\,\mathrm{m}} \, \, \mathbf{X}_{\,\mathrm{g}}^{\,\mathrm{T}\,0} \, & \, \mathbf{X}_{\,\mathrm{f}}^{\,\mathrm{T}\,0} \mathbf{X}_{\,\mathrm{m}} \, \, \mathbf{X}_{\,\mathrm{g}}^{\,\mathrm{T}\,0} \\ & & \mathbf{X}_{\,\mathrm{f}}^{\,\mathrm{T}\,2} \, \, \mathbf{X}_{\,\mathrm{m}} \, \, \mathbf{X}_{\,\mathrm{g}}^{\,\mathrm{T}\,2} \, + \mathbf{X}_{\,\mathrm{f}}^{\,\mathrm{T}\,2} \, \, \mathbf{X}_{\,\mathrm{m}} \, \, \mathbf{X}_{\,\mathrm{g}}^{\,\mathrm{T}\,2} \\ & + \, \, \frac{2}{12} \, \, \, \, \mathbf{X}_{\,\mathrm{f}}^{\,\mathrm{T}\,0} \mathbf{X}_{\,\mathrm{m}} \, \, \mathbf{X}_{\,\mathrm{g}}^{\,\mathrm{T}\,2} \, + \, \mathbf{X}_{\,\mathrm{f}}^{\,\mathrm{T}\,0} \mathbf{X}_{\,\mathrm{m}} \, \, \mathbf{X}_{\,\mathrm{g}}^{\,\mathrm{T}\,2} \\ & + \, \, \frac{2}{12} \, \, \, + \, \mathbf{X}_{\,\mathrm{f}}^{\,\mathrm{T}\,2} \, \mathbf{X}_{\,\mathrm{m}} \, \, \mathbf{X}_{\,\mathrm{g}}^{\,\mathrm{T}\,2} \, + \, \mathbf{X}_{\,\mathrm{f}}^{\,\mathrm{T}\,2} \, \mathbf{X}_{\,\mathrm{m}} \, \, \mathbf{X}_{\,\mathrm{g}}^{\,\mathrm{T}\,2} \end{array}$$

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- 1 P.H ohenberg and W .K ohn, Phys.Rev.136, 864 (1964).
- 2 W .K ohn and L.J. Sham , Phys.Rev.140, 1133 (1965).

⁵ J.C. Hubbard, Proc. Roy. Soc. A 276, 238 (1963).

⁹ A J. Lichtenstein and M J. Katsnelson, Phys. Rev. B 57, 6884 (1998).

³ V J. Anisim ov, J. Zaanen, and O K. Andersen, Phys. Rev. B 44, 943 (1991).

⁴ A. Svane and O. Gunnarsson, Phys. Rev. Lett. 65, 1148 (1990).

⁶ V J. Anisim ov, A J. Poteryaev, M A. Korotin, A D. Anokhin, and G. Kotliar, J. Phys.: Condens. M atter 35, 7359 (1997).

⁷ K. Held, IA. Nekrasov, N. Blumer, V. J. Anisimov, and D. Vollhardt, Int. J. Mod. Phys. B 15, 2611 (2001); K. Held, IA. Nekrasov, G. Keller, V. Eyert, N. Blumer, A. K. McMahan, R. T. Scalettar, T. Pruschke, V. J. Anisimov, and D. Vollhardt, cond-mat/0112079 (Published in Quantum Simulations of Complex Many-Body Systems: From Theory to Algorithms, eds. J. Grotendorst, D. Marks, and A. Muramatsu, NIC Series Volume 10 (NIC Directors, Forschunszentrum Julich, 2002) p. 175-209. (ISBN 3-00-009057-6)

⁸ K. Held, IA. Nekrasov, G. Keller, V. Eyert, N. Blum er, AK. McMahan, R.T. Scalettar, Th. Pruschke, V.I. Anisim ov, and D. Vollhardt, \Realistic investigations of correlated electron systems with LDA+DMFT", Psi-k New sletter 56 (April 2003), p. 65-103 [psi-kdlacuk/new sletters/New s.56/Highlight_56.pdf].

D. Vollhardt, in Cornelated Electron Systems, edited by V. J. Emery, World Scientic, Singapore, 1993, p. 57.

¹¹ G. Kotliar and D. Vollhardt, Physics Today 57, No. 3 (March), 53 (2004).

W. M etzner and D. Vollhardt, Phys. Rev. Lett. 62, 324 (1989).

A. Georges, G. Kotliar, W. Krauth, and M. Rozenberg, Rev. Mod. Phys. 68, 13 (1996).

M. H. Hettler, A. N. Tahvildar-Zadeh, M. Jarrell, T. Pruschke, and H. R. Krishnam urthy, Phys. Rev. B 58, R7475 (1998).

Th.M aier, M. Jarrell, Th.Pruschke and M.Hettler, Rev. Mod.Phys. (in print, cond-mat/0404055 (2004)).

¹⁶ S.Yu. Savrasov and G. Kotliar, Phys. Rev. B 69, 245101 (2004).

¹⁷ S.G. Ovchinnikov and I.S. Sandalov, Physica C 161, 607 (1989).

 $^{^{18}}$ V J.Em ery, Phys.Rev.Lett.58,2794 (1987).

¹⁹ C M .Varma, S.Sm itt-R ink, and E.A braham s, Solid State C om m un. 62, 681 (1987).

²⁰ S.V. Lovtsov and V.Yu. Yushankhai, Physica C 179, 159 (1991).

²¹ J.H. Je erson, H. Eskes, and L.F. Feiner, Phys. Rev. B 45, 7959 (1992).

²² H-B. Schuttler and A J. Fedro, Phys. Rev. B 45, R7588 (1992).

²³ V A. Gavrichkov, S.G. Ovchinnikov, A A. Borisov, and E.G. Goryachev, Zh. Eksp. Teor. Fiz. 118, 422 (2000); [JETP 91, 369 (2000)].

 $^{^{24}\,}$ V . G avrichkov, A . B orisov, and S G . O vch innikov, P hys.

- Rev.B 64,235124 (2001).
- 25 V A . G avrichkov, S.G. O vchinníkov, and L.E. Yakim ov, subm itted to JETP (2005).
- ²⁶ S.G. Ovchinnikov and O.G. Petrakovsky, J. Superconductivity 4, 437 (1991).
- 27 G H .W annier, Phys. Rev. 52, 191 (1937).
- N. Marzari and D. Vanderbilt, Phys. Rev. B 56, 12847 (1997).
- ²⁹ W ei Ku, H. Rosner, W E. Pickett, and R.T. Scalettar, Phys. Rev. Lett. 89, 167204 (2002).
- 30 O K. Andersen and O. Jepsen, Phys. Rev. Lett. 53, 2571 (1984).
- ³¹ V. J. Anisim ov, D. E. Kondakov, A. V. Kozhevnikov, I.A. Nekrasov, Z. V. Pchelkina, J.W. Allen, S.-K. Mo, H.-D. Kim, P. Metcalf, S. Suga, A. Sekiyama, G. Keller, I. Leonov, X. Ren, and D. Vollhardt, Phys. Rev. B. 71, 125119 (2005).
- ³² O. K. Andersen, Z. Paw low ska, and O. Jepsen, Phys Rev. B 34, 5253 (1986).
- ³³ P.G. Radaelli, D.G. Hinks, A.W. Mitchell, B.A. Hunter, J.L. Wagner, B. Dabrowski, K.G. Vandervoort, and H.K. Viswanathan, J.D. Jorgensen, Phys. Rev. B. 49, 4163 (1994).
- ³⁴ T. Kamiyama, F. Izumi, H. Takahashi, J.D. Jorgensen, B. Dabrowski, R.L. Hitterman, D.G. Hinks, H. Shaked, T.O. Mason, and M. Seabaugh, Physica C 229, 377–388 (1994).
- O. Gunnarsson, O.K. Andersen, O. Jepsen, and J. Zaanen, Phys. Rev. B. 39, 1708 (1989); V. I. Anisim ov and O. Gunnarsson, ibid: 43, 7570 (1991).
- ³⁶ V J. A nisim ov, M A. Korotin, IA. Nekrasov, Z.V. Pchelkina, and S. Sorella, Phys. Rev. B. 66, 100502 (R) (2002).
- ³⁷ Yu. Gaididei and V. Loktev, Phys. Status Solidi B 147, 307 (1988).
- ³⁸ A. Bianconi, M. De Santis, and A. DiCicco, A. M. Flank, A. Fontaine, and P. Lagarde, H. Katayama-Yoshida and A. Kotani, A. Marcelli, Phys. Rev. B. 38, R. 7196 (1988).
- H.Romberg, N.Nucker, M.Alexander, and J.Fink, D. Hahn, T.Zetterer, H.H.Otto, and K.F.Renk, Phys.Rev. B 41, R2609 (1990).
- ⁴⁰ C.T.Chen, L.H.Tjeng, J.Kwo, H.L.Kao, P.Rudolf, F. Sette, and R.M. Fleming, Phys.Rev.Lett. 68, 2543 (1992).
- ⁴¹ R.Raim ondiand JH.Je erson, LF.Feiner, Phys.Rev.B 53, 8774 (1996).
- 42 J.C. Hubbard, Proc. Roy. Soc. London A 277, 237 (1964).
- ⁴³ M. M. Korshunov, V. A. Gavrichkov, S.G. Ovchinnikov, Z.V. P. Chelkina, I.A. Nekrasov, M. A. Korotin, and V. J. Anisim ov, Zh. Eksp. Teor. Fiz. 126, 642 (2004) [JETP 99, 559 (2004)].
- ⁴⁴ M M . Korshunov, V A . Gavrichkov, S.G. Ovchinnikov, D . Manske, and I. Eremin, Physica C 402, 365 (2004).
- ⁴⁵ B.O. Wells, Z.-X. Shen, A. Matsuura, D. M. King, M. A. Kastner, M. Greven, and R. J. Birgeneau, Phys. Rev. Lett. 74, 964 (1995).
- ⁴⁶ C. Durr, S. Legner, R. Hayn, S.V. Borisenko, Z. Hu, A. Theresiak, M. Knupfer, M. S. Golden, J. Fink, F. Ronning, Z.-X. Shen, H. Eisaki, S. Uchida, C. Janowitz, R. Muller, R. L. Johnson, K. Rossnagel, L. Kipp, and G. Reichardt, Phys. Rev. B. 63, 014505 (2000).
- ⁴⁷ A A. Borisov, V A. Gavrichkov, and S.G. Ovchinnikov, M od. Phys. Lett. B 17, 479 (2003).
- ⁴⁸ A A.Borisov, V A.Gavrichkov, and S.G.Ovchinnikov, Zh. Eksp. Teor. Fiz. 124, 862 (2003); [JETP 97, 773 (2003)].
- ⁴⁹ A. Ino, T. M izokawa, and A. Fujim ori, K. Tamasaku, H. Eisaki, S. Uchida, T. Kimura, T. Sasagawa, and K. Kishio,

- Phys.Rev.Lett.79,2101 (1997).
- N. Harima, J. Matsuno, and A. Fujimori, Y. Onose, Y. Taguchi, and Y. Tokura, Phys. Rev B 64, 220507(R) (2001).
- A. Ino, C. Kim, M. Nakamura, T. Yoshida, T. Mizokawa, A. Fujimori, Z.-X. Shen, T. Kakeshita, H. Eisaki, and S. Uchida, Phys. Rev. B 65, 094504 (2002).
- N.P. Arm itage, D.H. Lu, C. Kim, A. Dam ascelli, K.M. Shen, F. Ronning, D.L. Feng, P. Bogdanov, and Z.-X. Shen, Y. Onose, Y. Taguchi, and Y. Tokura, P.K. M. ang, N. Kaneko, and M. Greven, Phys. Rev. Lett. 87, 147003 (2001).
- ⁵³ R.O. Zaitsev, Sov. Phys. JETP 41, 100 (1975).
- Yu A .Izum ov and B M .Letfullov, J.Phys.: C ondens.M atter 3, 5373 (1991).
- S.G. Ovchinnikov and V.V. Vaľkov, Hubbard Operators in the Theory of Strongly Correlated Electrons (Imperial College Press, London-Singapore, 2004).
- ⁵⁶ V.G. Bar'yakhtar, V.N.K rivoruchko, and D.A. Yablonskii, Green's Functions in Magnetism Theory [in Russian], (Nauk.Dumka, Kiev, 1984).
- ⁵⁷ O. K. Andersen, A.J. Liechtenstein, O. Jepsen, and F. Paulsen, J. Phys. Chem. Solids 56, 1573 (1995).
- ⁵⁸ E. Pavarini, I. Dasgupta, T. Saha-Dasgupta, O. Jepsen, and O. K. Andersen, Phys. Rev. Lett. 87, 047003 (2001).
- ⁵⁹ A S.M oskvin, J.M a'lek, M.K nupfer, R.N eudert, J.Fink, R. Hayn, S.-L.D rechsler, N.M otoyama, H.E isaki, and S. Uchida, Phys. Rev. Lett. 91, 037001 (2003).
- A S.M oskvin, Pis'm a v ZhETF 80,824 (2004) [JETP Lett. 80,697 (2004)].
- ⁶¹ T. Tohyam a and S. Maekawa, Phys. Rev. B 49, 3596 (1994).
- 62 S.G. Ovchinnikov, A.A. Borisov, V.A. Gavrichkov, and M.M. Korshunov, J. Phys.: Condens. Matter 16, L93 (2004).
- D. Vaknin, S. K. Sinha, D. E. Moncton, D. C. Johnston, J. M. Newsam, C. R. Sanya, and H. E. King, Jr., Phys. Rev. Lett. 58, 2802 (1987).
- ⁶⁴ JM. Tranquada, A H. Moudden, A J. Goldman, P. Zolliker, D E. Cox, and G. Shirane, S.K. Sinha, D. Vaknin, D.C. Johnston, M. S. Alvarez, A J. Jacobson, J.T. Lewandowski, and JM. Newsam, Phys. Rev. B 38, 2477 (1988).
- 65 T. Freltoft and G. Shirane, S.M itsuda, J.P. Remeika and A.S. Cooper, Phys. Rev. B 37, 137 (1988).
- ⁶⁶ P. Horsch and W. von der Linden, Z. Phys. B: Condens. M atter 72, 181 (1988).
- ⁶⁷ A A . K atanin and A P . K am pf, Phys. Rev. B 66, 100403 (R) (2003).
- ⁶⁸ L.N. Bulaevskii, E.L. Nagaev, D.I. Khom skii, Sov. Phys. JETP 54, 1562 (1968).
- ⁶⁹ K A. Chao, J. Spalek and A M. Oles, J. Phys. C:Sol. Stat. Phys. 10, 271 (1977).
- J.E. Hirsch, Phys. Rev. Lett. 54, 1317 (1985).
- 71 F.C.Zhang and T.M.Rice, Phys.Rev.B 41,7243 (1990).
- V J.Belinicher and A L.Chemyshev, Phys. Rev. B 47, 390 (1993).
- ⁷³ L.F. Feiner, J.H. Je erson, and R. Raim ondi, Phys. Rev. B 53, 8751 (1996).
- 74 A. Sherm an and M. Schreiber, Eur. Phys. J. B 32, 203 (2003).
- ⁷⁵ X J. Zhou, T. Yoshida, A. Lanzara, P.V. Bogdanov, S.A. Kellar, K.M. Shen, W. L. Yang, F. Ronning, T. Sasagawa, T. Kakeshita, T. Noda, H. Eisaki, S. Uchida, C.T. Lin, F.

Zhou, JW . Xiong, W X. Ti, ZX. Zhao, A. Fujim ori, Z. Hussain and Z.-X. Shen, Nature 423, 398 (2003).